

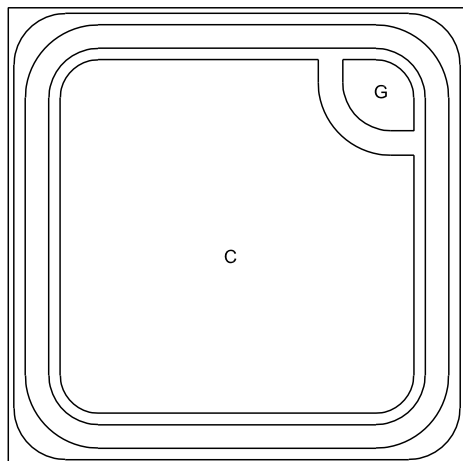
PROCESS CPS150
Silicon Controlled Rectifier
25 Amp Sensitive Gate SCR Chip



PROCESS DETAILS

Process	GLASS PASSIVATED MESA
Die Size	150 x 150 MILS
Die Thickness	8.7 MILS
Cathode Bonding Pad Area	117 x 84 MILS
Gate Bonding Pad Area	24 x 24 MILS
Top Side Metalization	Al - 45,000Å
Back Side Metalization	Al/Mo/Ni/Ag - 32,000Å

GEOMETRY



BACKSIDE ANODE R0

GROSS DIE PER 4 INCH WAFER

466

PRINCIPAL DEVICE TYPES

CS220-25M Series

CSDD-25M Series

R1 (29-April 2010)